



# PMZ600UNEL

20 V, N-channel Trench MOSFET

28 June 2016

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Low leakage current
- Leadless ultra small SMD plastic package:  $1.0 \times 0.6 \times 0.48$  mm
- ElectroStatic Discharge (ESD) protection  $> 1$  kV HBM
- Drain-source on-state resistance  $R_{DSon} = 470$  m $\Omega$

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

## 4. Quick reference data

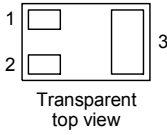
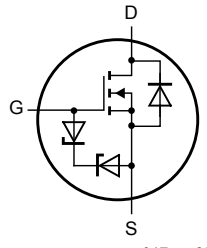
Table 1. Quick reference data

| Symbol                        | Parameter                        | Conditions                                     |     | Min | Typ | Max | Unit       |
|-------------------------------|----------------------------------|------------------------------------------------|-----|-----|-----|-----|------------|
| $V_{DS}$                      | drain-source voltage             | $T_J = 25$ °C                                  |     | -   | -   | 20  | V          |
| $V_{GS}$                      | gate-source voltage              |                                                |     | -8  | -   | 8   | V          |
| $I_D$                         | drain current                    | $V_{GS} = 4.5$ V; $T_{amb} = 25$ °C            | [1] | -   | -   | 0.6 | A          |
| <b>Static characteristics</b> |                                  |                                                |     |     |     |     |            |
| $R_{DSon}$                    | drain-source on-state resistance | $V_{GS} = 4.5$ V; $I_D = 0.6$ A; $T_J = 25$ °C |     | -   | 470 | 620 | m $\Omega$ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                                                             | Graphic symbol                                                                                       |
|-----|--------|-------------|------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------|
| 1   | G      | gate        |  <p>Transparent top view</p> <p><b>DFN1006-3 (SOT883)</b></p> |  <p>017aaa255</p> |
| 2   | S      | source      |                                                                                                                                                |                                                                                                      |
| 3   | D      | drain       |                                                                                                                                                |                                                                                                      |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package   |                                                                 |         |
|-------------|-----------|-----------------------------------------------------------------|---------|
|             | Name      | Description                                                     | Version |
| PMZ600UNEL  | DFN1006-3 | DFN1006-3: leadless ultra small plastic package; 3 solder lands | SOT883  |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMZ600UNEL  | L3           |

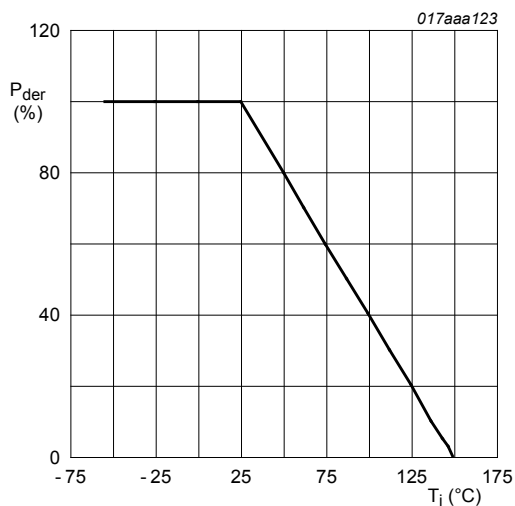
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

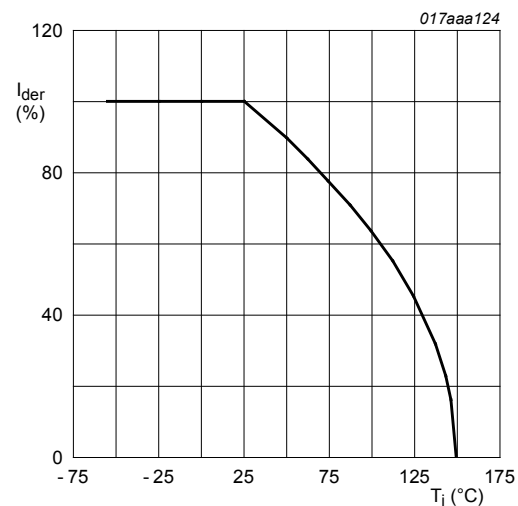
| Symbol                    | Parameter               | Conditions                                                     |     | Min | Max  | Unit |
|---------------------------|-------------------------|----------------------------------------------------------------|-----|-----|------|------|
| V <sub>DS</sub>           | drain-source voltage    | T <sub>j</sub> = 25 °C                                         |     | -   | 20   | V    |
| V <sub>GS</sub>           | gate-source voltage     |                                                                |     | -8  | 8    | V    |
| I <sub>D</sub>            | drain current           | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C              | [1] | -   | 0.6  | A    |
|                           |                         | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C             | [1] | -   | 0.4  | A    |
| I <sub>DM</sub>           | peak drain current      | T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs |     | -   | 2.5  | A    |
| P <sub>tot</sub>          | total power dissipation | T <sub>amb</sub> = 25 °C                                       | [2] | -   | 360  | mW   |
|                           |                         |                                                                | [1] | -   | 715  | mW   |
|                           |                         | T <sub>sp</sub> = 25 °C                                        |     | -   | 2700 | mW   |
| T <sub>j</sub>            | junction temperature    |                                                                |     | -55 | 150  | °C   |
| T <sub>amb</sub>          | ambient temperature     |                                                                |     | -55 | 150  | °C   |
| T <sub>stg</sub>          | storage temperature     |                                                                |     | -65 | 150  | °C   |
| <b>Source-drain diode</b> |                         |                                                                |     |     |      |      |
| I <sub>S</sub>            | source current          | T <sub>amb</sub> = 25 °C                                       | [1] | -   | 0.4  | A    |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.  
 [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



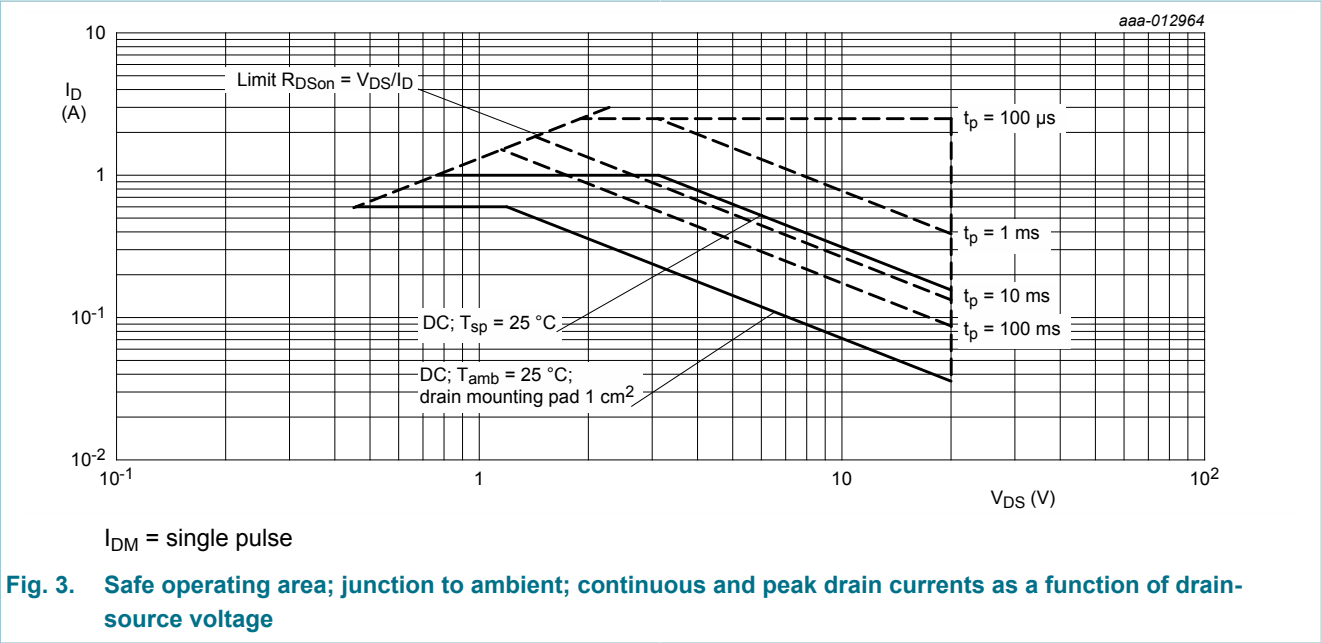
**Fig. 1. Normalized total power dissipation as a function of junction temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$



**Fig. 2. Normalized continuous drain current as a function of junction temperature**

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

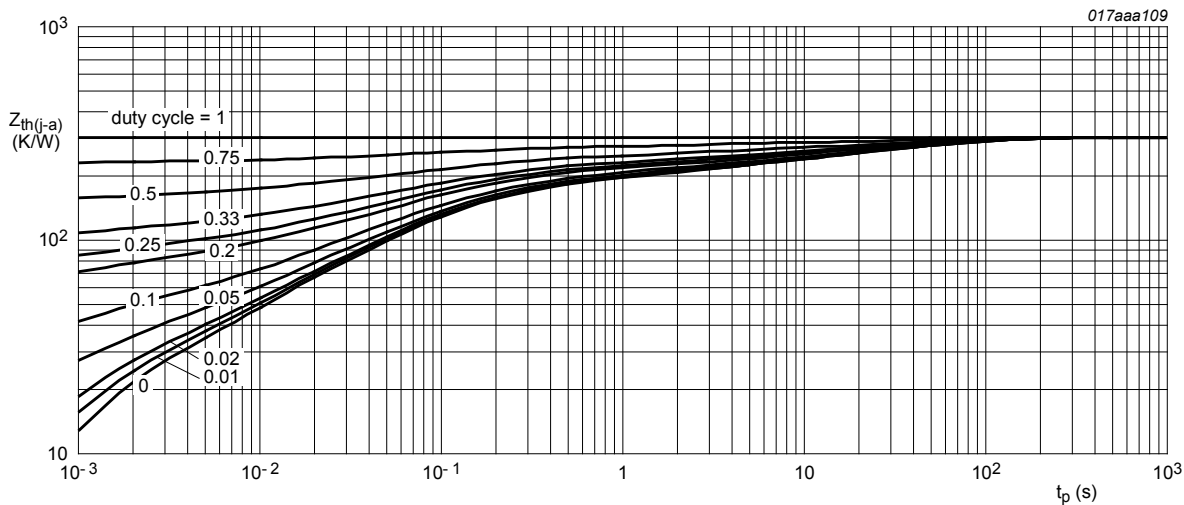


9. Thermal characteristics

Table 6. Thermal characteristics

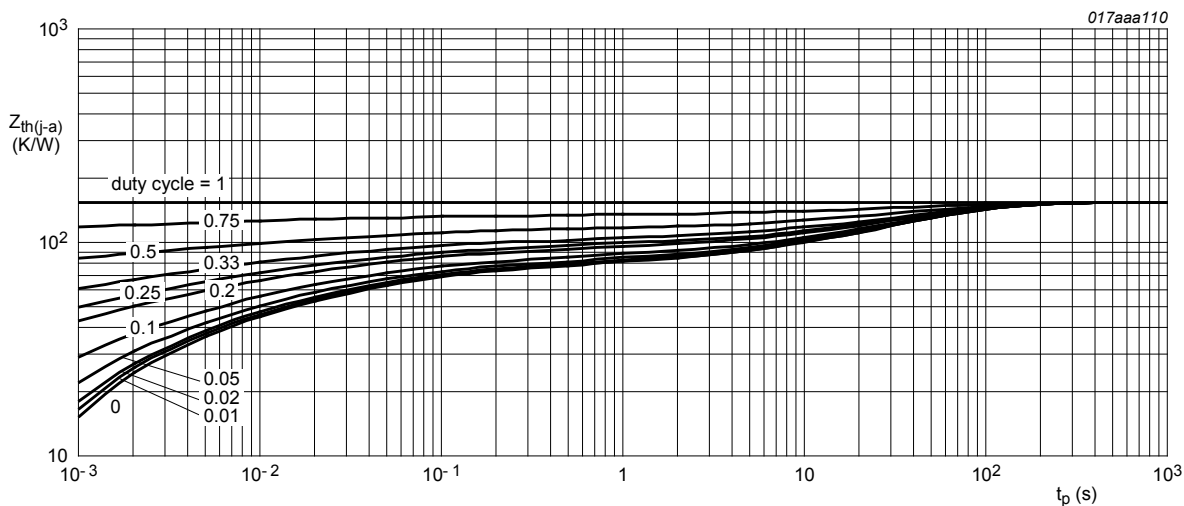
| Symbol                | Parameter                                        | Conditions  |     | Min | Typ | Max | Unit |
|-----------------------|--------------------------------------------------|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance from junction to ambient      | in free air | [1] | -   | 305 | 360 | K/W  |
|                       |                                                  |             | [2] | -   | 150 | 175 | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |             |     | -   | -   | 40  | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.  
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

| Symbol                         | Parameter                        | Conditions                                                                                              | Min  | Typ  | Max  | Unit       |
|--------------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------|------|------|------|------------|
| <b>Static characteristics</b>  |                                  |                                                                                                         |      |      |      |            |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage   | $I_D = 250\ \mu A$ ; $V_{GS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                             | 20   | -    | -    | V          |
| $V_{GSth}$                     | gate-source threshold voltage    | $I_D = 250\ \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25\ ^\circ C$                                           | 0.45 | 0.7  | 0.95 | V          |
| $I_{DSS}$                      | drain leakage current            | $V_{DS} = 20\ V$ ; $V_{GS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                               | -    | -    | 1    | $\mu A$    |
|                                |                                  | $V_{DS} = 20\ V$ ; $V_{GS} = 0\ V$ ; $T_j = 150\ ^\circ C$                                              | -    | -    | 10   | $\mu A$    |
|                                |                                  | $V_{DS} = 5\ V$ ; $V_{GS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                                | -    | -    | 25   | nA         |
| $I_{GSS}$                      | gate leakage current             | $V_{GS} = 8\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                                | -    | -    | 10   | $\mu A$    |
|                                |                                  | $V_{GS} = -8\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                               | -    | -    | -10  | $\mu A$    |
|                                |                                  | $V_{GS} = 4.5\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                              | -    | -    | 1    | $\mu A$    |
|                                |                                  | $V_{GS} = -4.5\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                             | -    | -    | -1   | $\mu A$    |
|                                |                                  | $V_{GS} = 1.8\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                              | -    | -    | 50   | nA         |
|                                |                                  | $V_{GS} = -1.8\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                             | -    | -    | -50  | nA         |
| $R_{DSon}$                     | drain-source on-state resistance | $V_{GS} = 4.5\ V$ ; $I_D = 0.6\ A$ ; $T_j = 25\ ^\circ C$                                               | -    | 470  | 620  | m $\Omega$ |
|                                |                                  | $V_{GS} = 4.5\ V$ ; $I_D = 0.6\ A$ ; $T_j = 150\ ^\circ C$                                              | -    | 760  | 1000 | m $\Omega$ |
|                                |                                  | $V_{GS} = 2.5\ V$ ; $I_D = 0.5\ A$ ; $T_j = 25\ ^\circ C$                                               | -    | 620  | 850  | m $\Omega$ |
|                                |                                  | $V_{GS} = 1.8\ V$ ; $I_D = 0.1\ A$ ; $T_j = 25\ ^\circ C$                                               | -    | 845  | 1300 | m $\Omega$ |
|                                |                                  | $V_{GS} = 1.5\ V$ ; $I_D = 10\ mA$ ; $T_j = 25\ ^\circ C$                                               | -    | 1125 | 3000 | m $\Omega$ |
|                                |                                  | $V_{GS} = 1.2\ V$ ; $I_D = 1\ mA$ ; $T_j = 25\ ^\circ C$                                                | -    | 2210 | -    | m $\Omega$ |
| $g_{fs}$                       | forward transconductance         | $V_{DS} = 5\ V$ ; $I_D = 0.6\ A$ ; $T_j = 25\ ^\circ C$                                                 | -    | 1    | -    | S          |
| $R_G$                          | gate resistance                  | $f = 1\ MHz$                                                                                            | -    | 34   | -    | $\Omega$   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                         |      |      |      |            |
| $Q_{G(tot)}$                   | total gate charge                | $V_{DS} = 10\ V$ ; $I_D = 0.6\ A$ ; $V_{GS} = 4.5\ V$ ; $T_j = 25\ ^\circ C$                            | -    | 0.4  | 0.7  | nC         |
| $Q_{GS}$                       | gate-source charge               |                                                                                                         | -    | 0.1  | -    | nC         |
| $Q_{GD}$                       | gate-drain charge                |                                                                                                         | -    | 0.1  | -    | nC         |
| $C_{iss}$                      | input capacitance                | $V_{DS} = 10\ V$ ; $f = 1\ MHz$ ; $V_{GS} = 0\ V$ ; $T_j = 25\ ^\circ C$                                | -    | 21.3 | -    | pF         |
| $C_{oss}$                      | output capacitance               |                                                                                                         | -    | 5.4  | -    | pF         |
| $C_{rss}$                      | reverse transfer capacitance     |                                                                                                         | -    | 4.2  | -    | pF         |
| $t_{d(on)}$                    | turn-on delay time               | $V_{DS} = 10\ V$ ; $I_D = 0.6\ A$ ; $V_{GS} = 4.5\ V$ ; $R_{G(ext)} = 6\ \Omega$ ; $T_j = 25\ ^\circ C$ | -    | 5.6  | -    | ns         |
| $t_r$                          | rise time                        |                                                                                                         | -    | 9.2  | -    | ns         |

| Symbol              | Parameter            | Conditions                                                             |  | Min | Typ | Max | Unit |
|---------------------|----------------------|------------------------------------------------------------------------|--|-----|-----|-----|------|
| t <sub>d(off)</sub> | turn-off delay time  |                                                                        |  | -   | 19  | -   | ns   |
| t <sub>f</sub>      | fall time            |                                                                        |  | -   | 51  | -   | ns   |
| Source-drain diode  |                      |                                                                        |  |     |     |     |      |
| V <sub>SD</sub>     | source-drain voltage | I <sub>S</sub> = 0.36 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C |  | -   | 0.8 | 1.2 | V    |

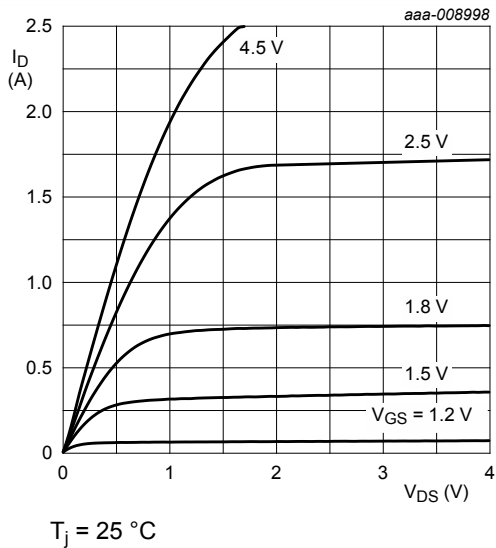


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

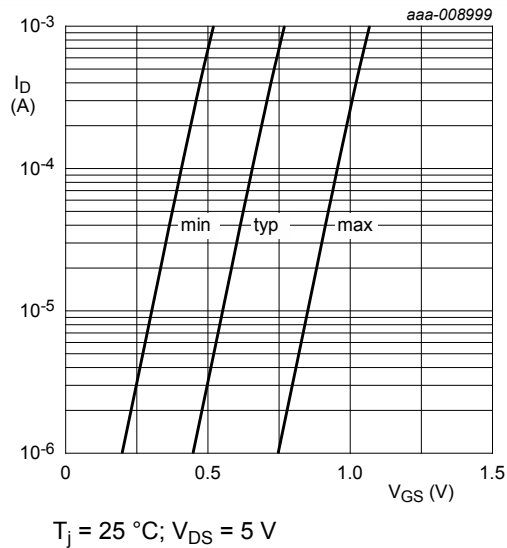


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

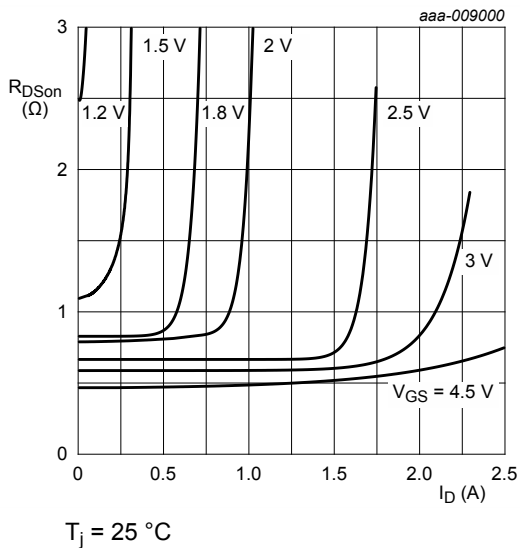


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

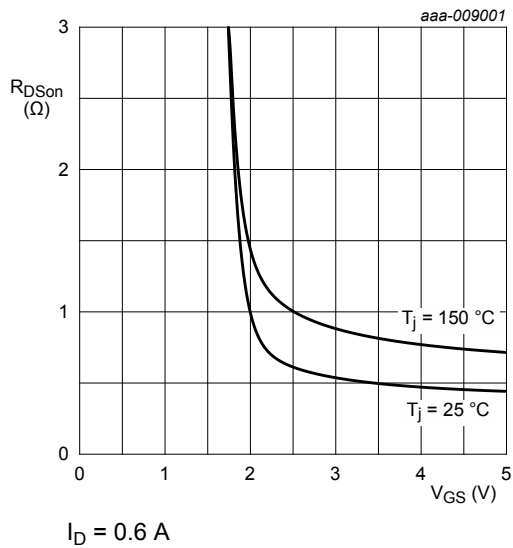


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

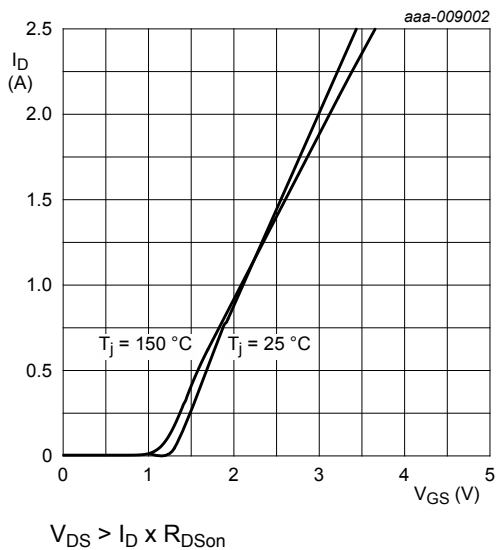


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

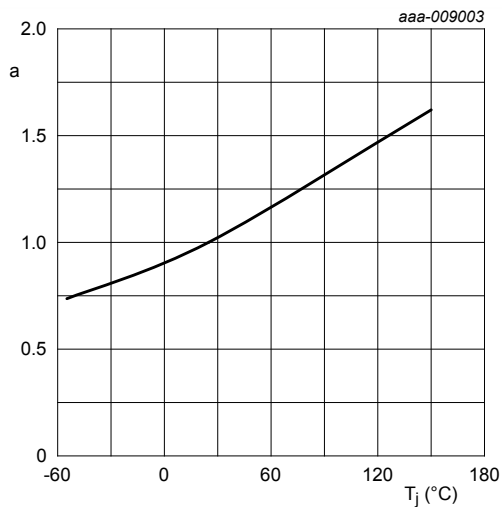


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

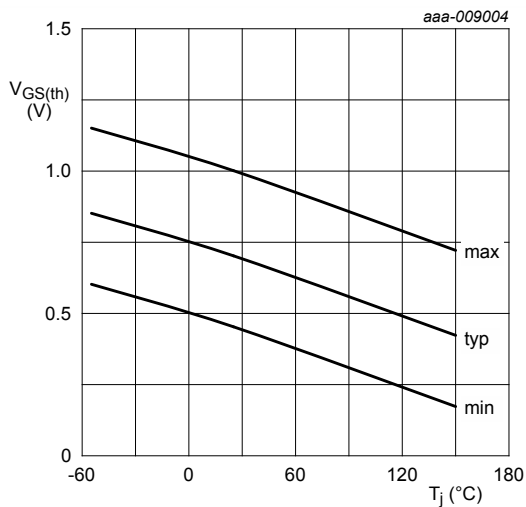


Fig. 12. Gate-source threshold voltage as a function of junction temperature

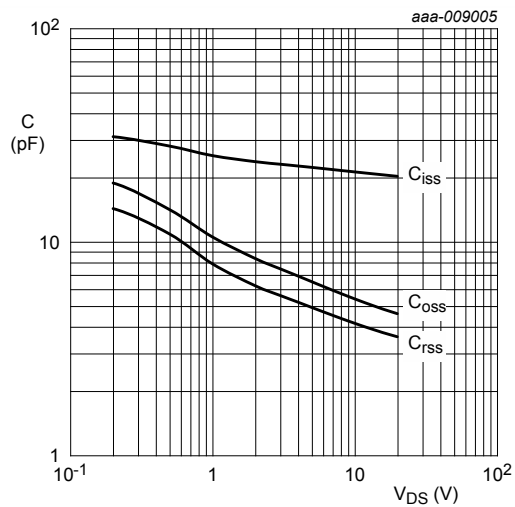


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

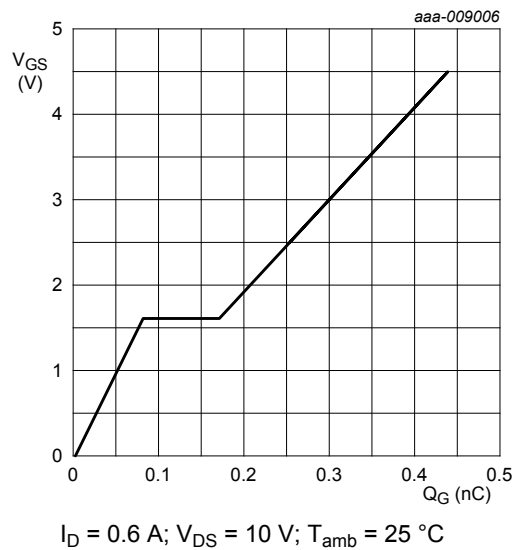


Fig. 14. Gate-source voltage as a function of gate charge; typical values



Fig. 15. MOSFET transistor: Gate charge waveform definitions

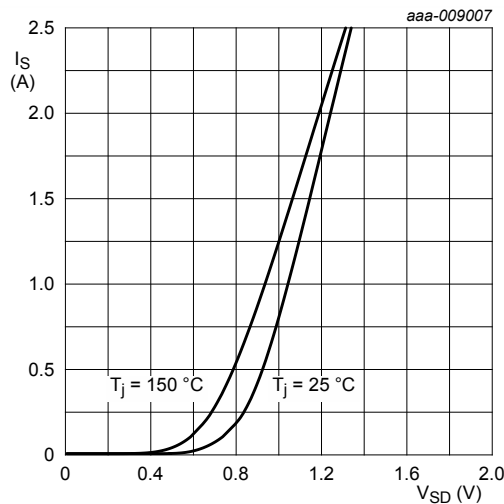


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

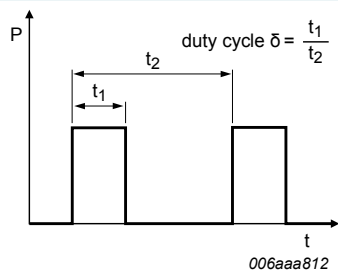


Fig. 17. Duty cycle definition

12. Package outline

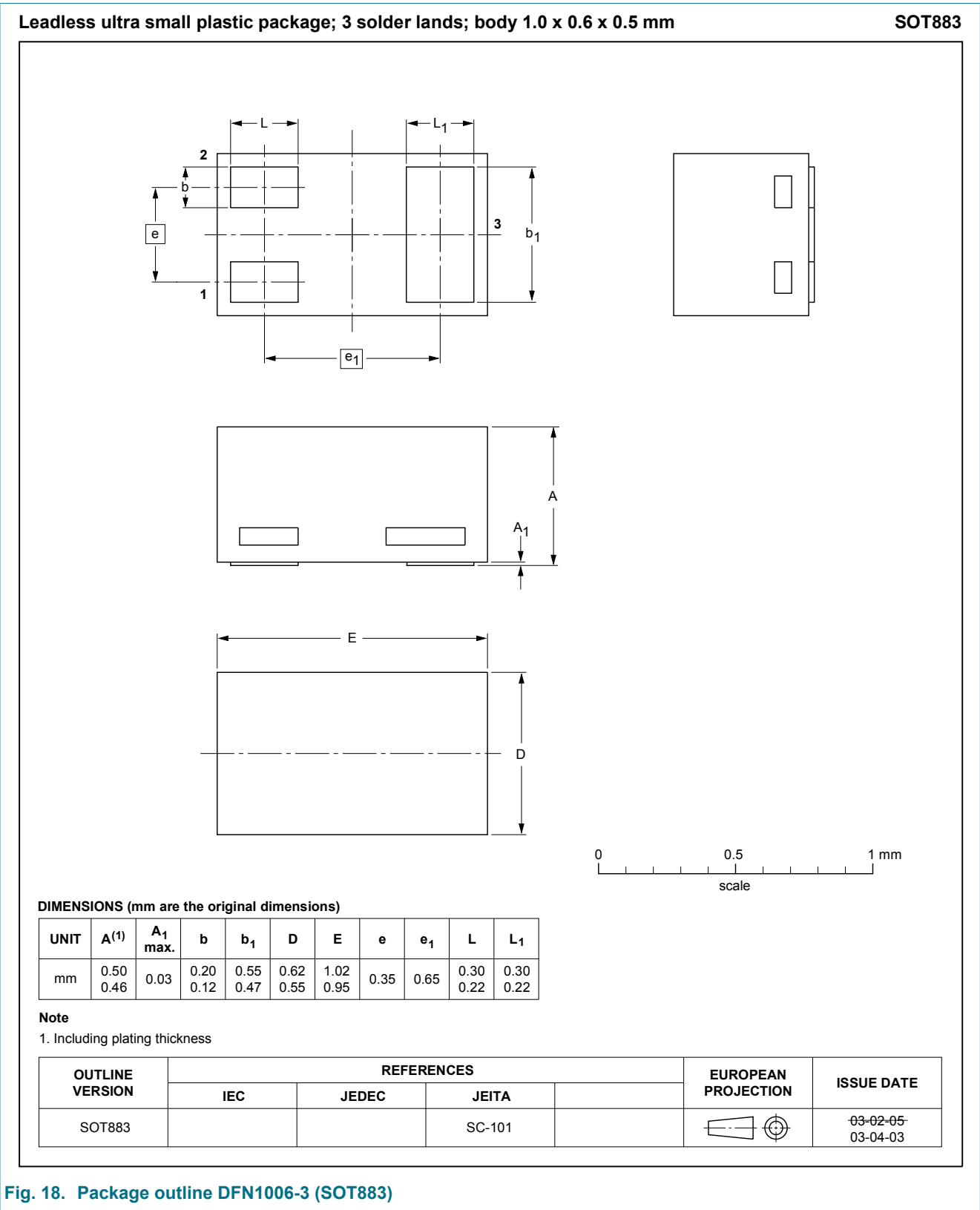
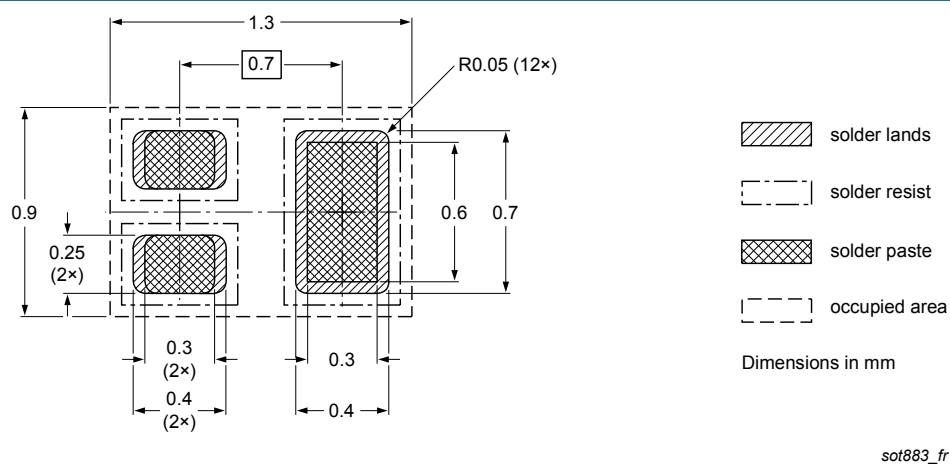


Fig. 18. Package outline DFN1006-3 (SOT883)

## 13. Soldering



**Fig. 19. Reflow soldering footprint for DFN1006-3 (SOT883)**

## 14. Revision history

Table 8. Revision history

| Data sheet ID  | Release date | Data sheet status  | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMZ600UNEL v.1 | 20160628     | Product data sheet | -             | -          |

## 15. Legal information

### 15.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
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Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,  
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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